



Silicon Photo Multipliers as readout for the NA62 CEDAR Detector

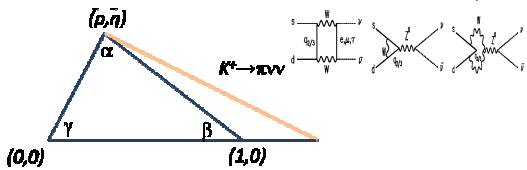
The NA62 Collaboration



(Bern ITP, Birmingham, CERN, Dubna, Fairfax, Ferrara, Florence, Frascati, Louvain, Mainz, Menlo Park, Merced, Moscow, Naples, Perugia, Pisa, Protvino, Rome I&II, S.Luis Potosi, Sofia, Turin, Vancouver)

THEORY

- $K^+ \rightarrow \pi^+ \nu \bar{\nu}$ BR measures one side of CKM triangle
- Theoretical prediction depending on top (dominant) and charm contributions in loops

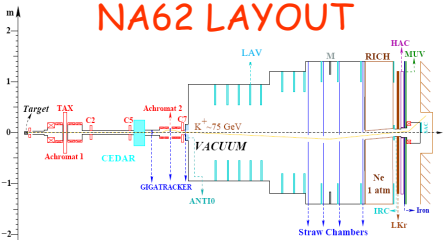


$$BR(K^+ \rightarrow \pi^+ \nu \bar{\nu})_{THEORY} = (8.22 \pm 0.84) \cdot 10^{-11}$$

$$BR(K^+ \rightarrow \pi^+ \nu \bar{\nu})_{EXP} = (1.73^{+1.15}_{-1.05}) \cdot 10^{-10} \text{ (7 candidates)}$$

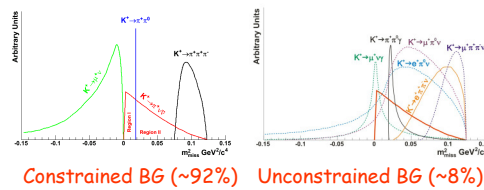
E787/E949, Phys.Rev.Lett.101, 191082(2008)

NA62 LAYOUT



- CEDAR: On-beam Kaon tagging through Cherenkov effect
- GIGATRACKER: hi-res P_k measurement, sub-ns resolution
- VETOES: 12 stations to veto particles from BG decays
- STRAW CHAMBERS: Track momentum at $<1\%$ resolution

- LKR: γ rejection at $[10^{-3}-10^{-5}]$ level for $E_\gamma=[2.5-10]$ GeV
- HAC/MUV: μ^+ reco (MUV), $E(\pi^+)$ deposit analysis (HAC)



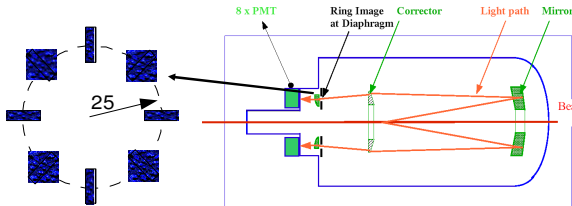
Constrained BG (~92%) Unconstrained BG (~8%)

NA62 GOALS

- Collect ~ 100 $K^+ \rightarrow \pi^+ \nu \bar{\nu}$ events with $\sim 10\%$ BG in 2 years
- High efficiency in rejecting photons and muons from Kaon decays

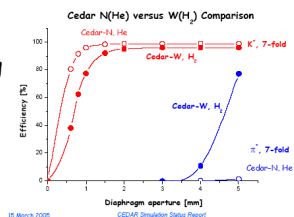
CEDAR(ChErenkov Differential counter with Achromatic Ring focus)

- Used at CERN since 70s to tag on-beam particles
- Optics condenses light into 8 spots ($1 \times 3 \text{ cm}^2$ each)
- 6(or 7)/8 spot coincidence



CHANGES FOR NA62:

- Hydrogen filling to reduce multiple scattering
- Readout and electronics to be renewed



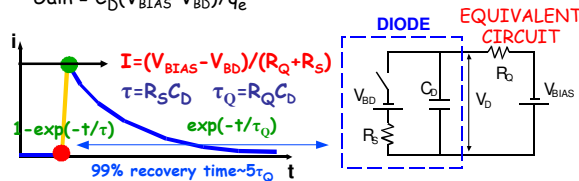
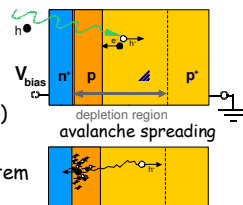
READOUT REQUIREMENTS

- $R_{Kaon} \sim 50 \text{ MHz}$ ($R_{TOT} \sim 1 \text{ GHz}$)
- $R_\gamma \sim 2 \text{ MHz/mm}^2$ (on spots)
- Kaon tag Eff. $> 95\%$
- Contamination $< 10^{-6}$
- Time resolution $< 100 \text{ ps}$

SPAD (Single Photon Avalanche Diodes)

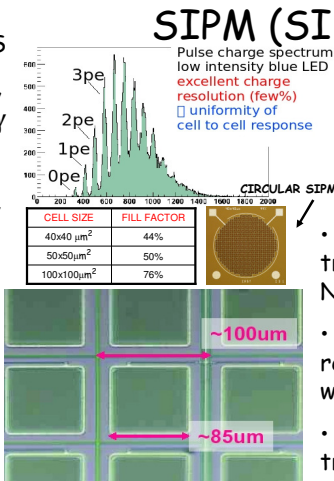
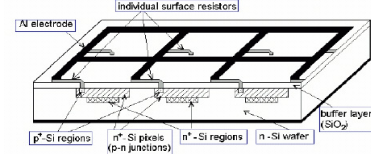
Diodes working in the discharge (Geiger) regime

- Diode Bias V_{BIAS} above V_{BD}
- Photoelectron triggers avalanche
- I quenching through R_Q ($\gg R_S$) required to detect other p.e.
- It is a BINARY (trigger) system
- Gain = $C_D(V_{BIAS}-V_{BD})/q_e$



A SIPM is a MATRIX of SPADS

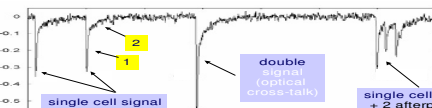
- Single SPADs (cells) independent, give the same signal when hit by a γ
- Several hundred cells/mm²
- Output charge proportional to N_γ
- Small % of dead surface
- Σ (digital signals) = analog signal



CELL SIZE	FILL FACTOR
40x40 μm^2	44%
50x50 μm^2	50%
100x100 μm^2	76%

SIPM (SIlicon PhotoMultiplier)

NOISE

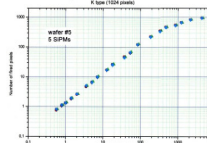


EFFICIENCY

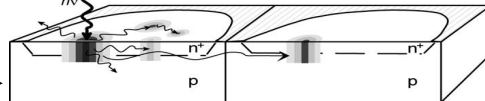
$\sim 70\%$ for SIPMs, depends on dead material, quantum eff. and shower trigger probability

DYNAMICAL RANGE

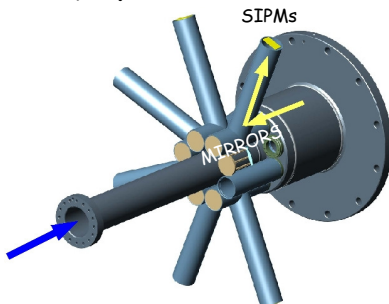
Output proportional to N_γ unless $N_\gamma < \# \text{CELLS}$



- Dark count: free carriers can trigger avalanches, depends on $N_{CELL}/SIPM$, $R_{DC} \sim 1 \text{ MHz}$
- Afterpulse: Due to carrier releasing by traps, increases with radiation
- Cross-Talk: Signal in a cell triggers neighbour cells



SIPMs for CEDAR readout



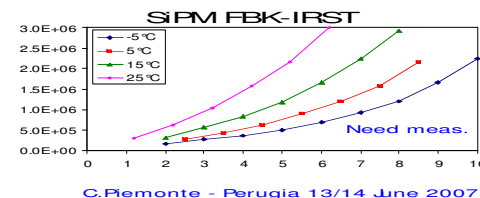
Cherenkov light can be redirected far from the quartz window using mirrors to:

- reduce radiation damages
- concentrate Ch. light on a smaller surface to reduce the SIPM dimensions

NOISE

DARK CURRENT: 500 KHz/mm² @ T=300K

- Moderate cooling (T=250/200K) required
- Lower gain (lower V_{BIAS}) to reduce DC
- Larger cells, coincidences among them

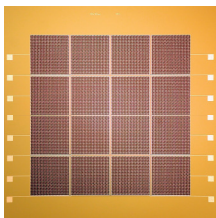


AFTER-PULSES: not an issue (+1 MHz/spot)
CROSS-TALK: well below 1%

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Assuming to place on each CEDAR spot a 4x4 matrix of 3x3 mm² and 900 channel SIPM one gets:

- PDE $\times 3$ wrt using normal PMs (but SIPMs are less sensible to UV); PDE is a function of spectrum
- 10 Cherenkov photons @ 50 MHz, i.e. 3 photoelectrons/spot, i.e. 10MHz/channel (single γ)
- Detection efficiency for 3 p.e./spot and using 6(7)/8 coincidence method is $\gg 95\%$



Even though full recovery time of a single cell is $\sim 100 \text{ ns}$, the high number of channels allows to stand a rate of $\sim 100 \text{ MHz/mm}^2$ (single γ)